KTA968A TRANSISTOR (PNP)

TO-220C

1.BASE
2.COLLECTOR
3.EMITTER

FEATURES

- High Transition Frequency
- High Voltage Applications

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-180	V
V_{CEO}	Collector-Emitter Voltage	-180	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-1.5	A
P_C	Collector Power Dissipation	2	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	63	℃/W
T_j,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA,I_E=0	-180			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA,I_B=0	-180			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-1mA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-160V,I_E=0			-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-1	μA
DC current gain	h_{FE}	V_{CE}=-5V, I_C=-100mA	70		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA,I_B=-50mA			-1.5	V
Base-emitter voltage	V_{BE}	V_{CE}=-5V, I_C=-500mA			-1	V
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0, f=1MHz		30		pF
Transition frequency	f_T	V_{CE}=-10V,I_C=-100mA		100		MHz

CLASSIFICATION OF h_{FE}

RANK	O	Y
RANGE	70-140	120-240